Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage ③	600	----	----	V	V_{GE} = 0V, I_C = 250µA
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	----	0.67	----	V/°C	V_{GE} = 0V, I_C = 1.0mA
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	----	1.85	2.1	V	I_C = 11A V_{GE} = 15V
		----	2.46	----		I_C = 18A See Fig. 2, 5
		----	2.07	----		I_C = 11A, T_J = 150°C
$V_{GE(th)}$	Gate Threshold Voltage	4.0	----	6.5		V_{CE} = V_{GE}, I_C = 250µA
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	----	-11	----	mV/°C	V_{CE} = V_{GE}, I_C = 250µA
g_{fe}	Forward Transconductance ④	3.0	3.6	----	S	V_{CE} = 100V, I_C = 11A
I_{CES}	Zero Gate Voltage Collector Current	----	----	250	µA	V_{GE} = 0V, V_{CE} = 600V
		----	----	2500		V_{GE} = 0V, V_{CE} = 600V, T_J = 150°C
V_{FM}	Diode Forward Voltage Drop	----	1.4	1.7	V	I_C = 8.0A See Fig. 13
		----	1.3	1.6		I_C = 8.0A, T_J = 150°C
I_{GES}	Gate-to-Emitter Leakage Current	----	----	±100	nA	V_{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	----	39	59		I_C = 11A
Qge	Gate - Emitter Charge (turn-on)	----	5.3	8.0	nC	V_{CC} = 400V See Fig. 8
Q_{gc}	Gate - Collector Charge (turn-on)	----	20	30		V_{GE} = 15V
$t_{d(on)}$	Turn-On Delay Time	----	21	----		T_J = 25°C
t_r	Rise Time	----	37	----	ns	I_C = 11A, V_{CC} = 480V
$t_{d(off)}$	Turn-Off Delay Time	----	463	690		V_{GE} = 15V, R_G = 50Ω
t_f	Fall Time	----	340	510		Energy losses include "tail" and
E_{on}	Turn-On Switching Loss	----	0.41	----		diode reverse recovery.
E_{off}	Turn-Off Switching Loss	----	2.03	----	mJ	See Fig. 9, 10, 11, 18
E_{ts}	Total Switching Loss	----	2.44	3.7		
$t_{d(on)}$	Turn-On Delay Time	----	19	----		T_J = 150°C, See Fig. 9, 10, 11, 18
t_r	Rise Time	----	41	----	ns	I_C = 6.5A, V_{CC} = 480V
$t_{d(off)}$	Turn-Off Delay Time	----	590	----		V_{GE} = 15V, R_G = 50Ω
t_f	Fall Time	----	600	----		Energy losses include "tail" and
E_{ts}	Total Switching Loss	----	3.49	----	mJ	diode reverse recovery.
L_E	Internal Emitter Inductance	----	7.5	----	nH	Measured 5mm from package
C_{ies}	Input Capacitance	----	460	----		V_{GE} = 0V
C_{oes}	Output Capacitance	----	54	----	pF	V_{CC} = 30V See Fig. 7
C_{res}	Reverse Transfer Capacitance	----	14	----		f = 1.0MHz
t_{rr}	Diode Reverse Recovery Time	----	37	55	ns	T_J = 25°C See Fig.
		----	55	90		T_J = 125°C 14 I_F = 8.0A
I_{rr}	Diode Peak Reverse Recovery Current	----	3.5	5.0	A	T_J = 25°C See Fig.
		----	4.5	8.0		T_J = 125°C 15 V_R = 200V
Q_{rr}	Diode Reverse Recovery Charge	----	65	138	nC	T_J = 25°C See Fig.
		----	124	360		T_J = 125°C 16 di/dt 200A/µs
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery	----	240	----	A/µs	T_J = 25°C See Fig.
	During t_b	----	210	----		T_J = 125°C 17

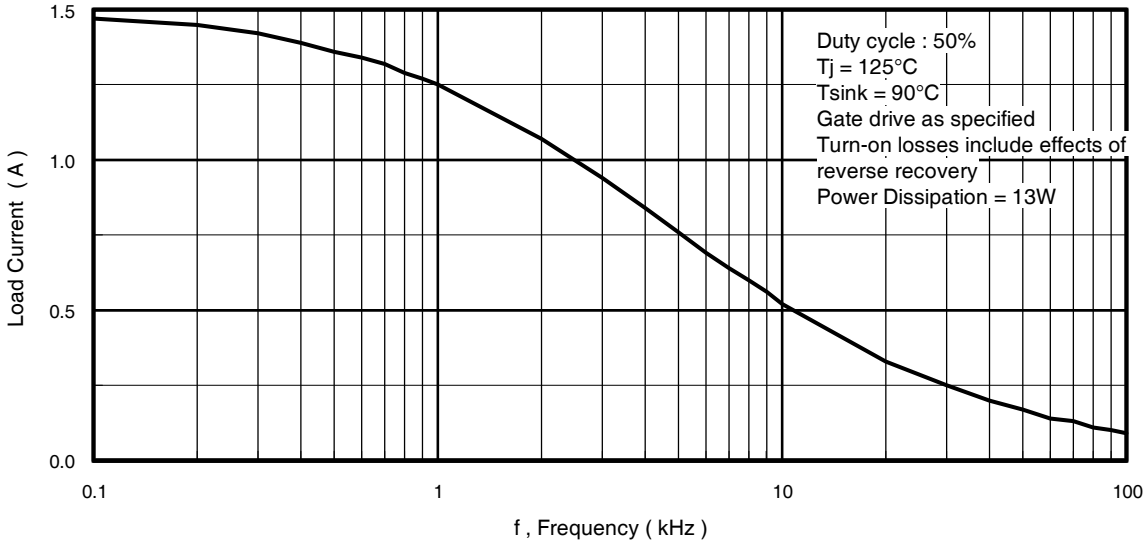


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

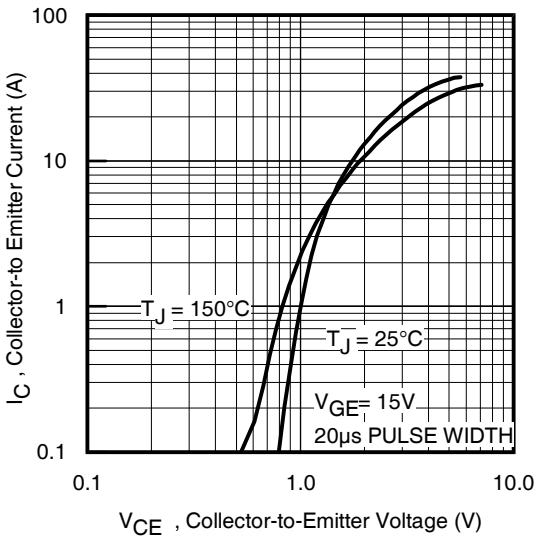


Fig. 2 - Typical Output Characteristics

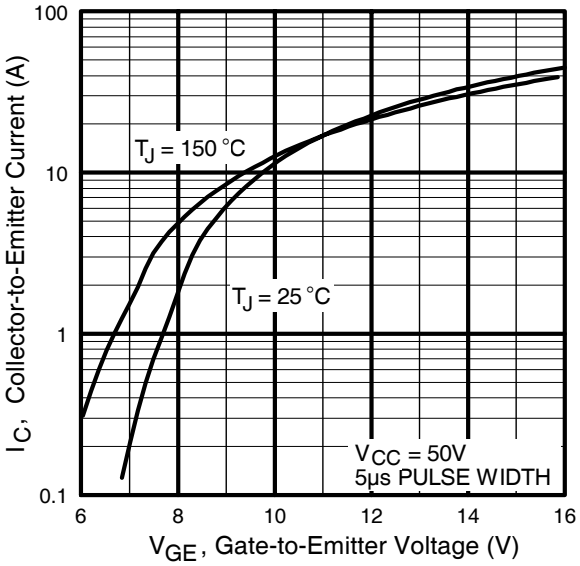


Fig. 3 - Typical Transfer Characteristics

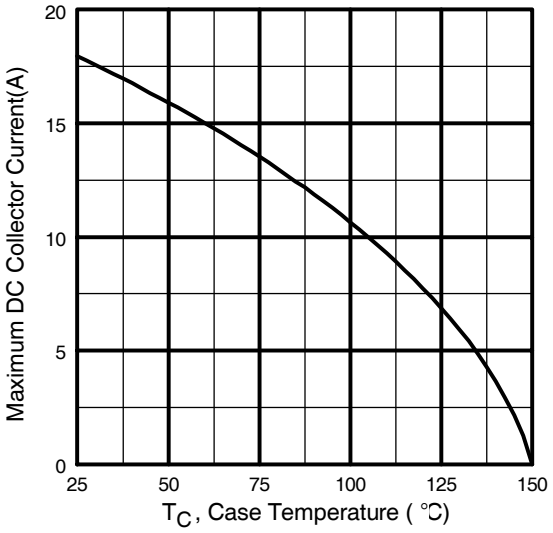


Fig. 4 - Maximum Collector Current vs. Case Temperature

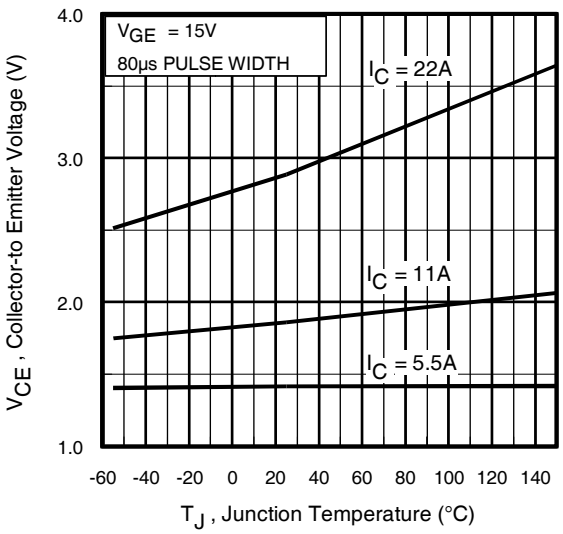


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

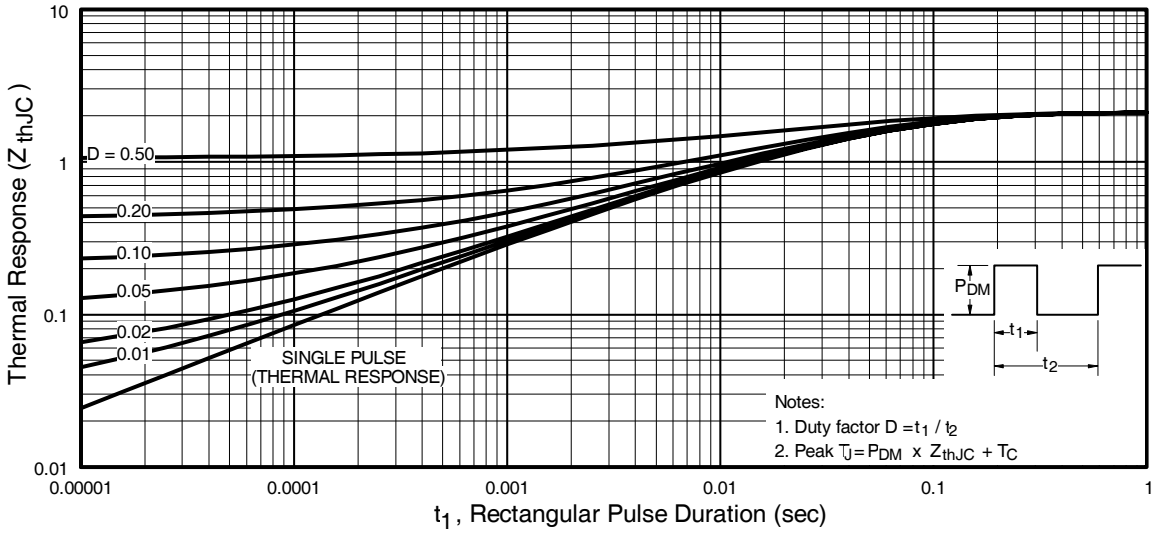


Fig. 6 - Maximum IGBT Effective Transient Thermal Impedance, Junction-to-Case

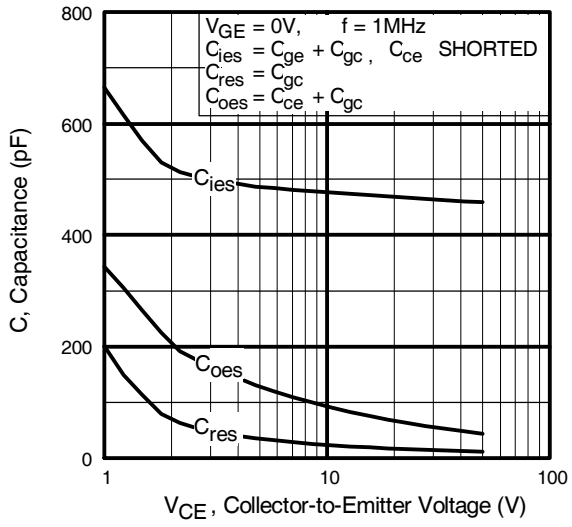


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

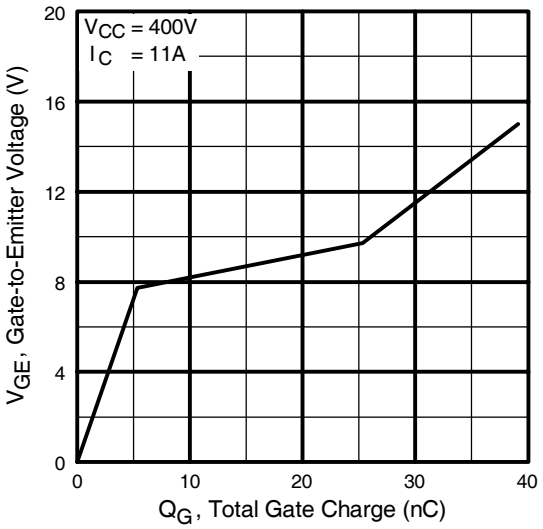


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

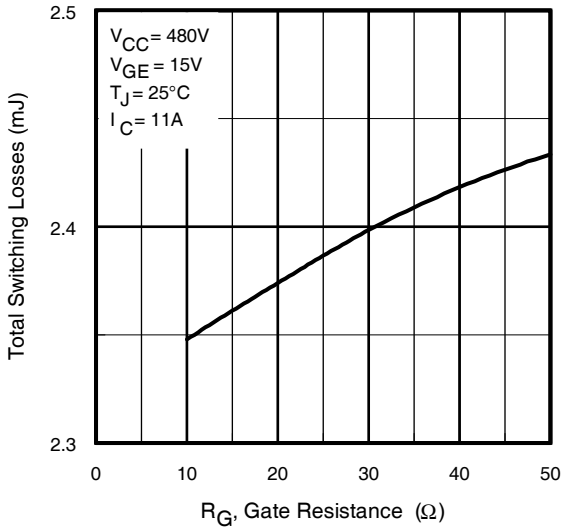


Fig. 9 - Typical Switching Losses vs. Gate Resistance

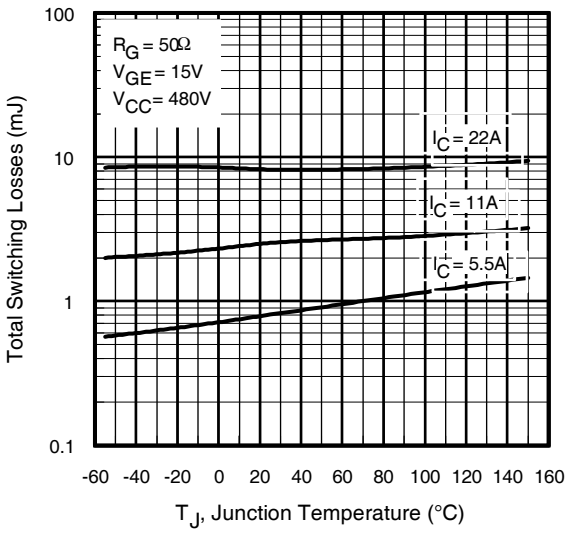


Fig. 10 - Typical Switching Losses vs. Junction Temperature

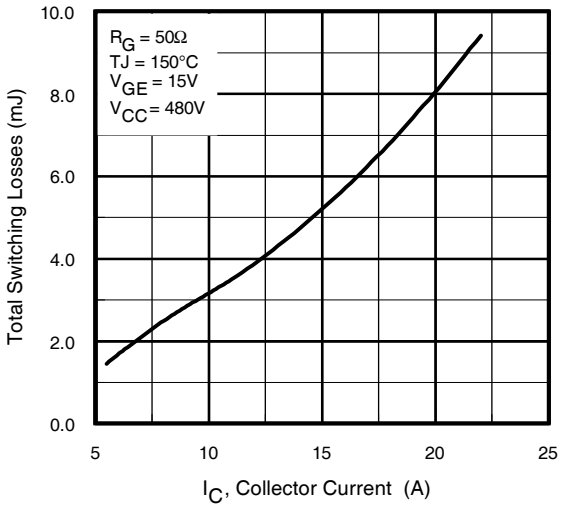


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

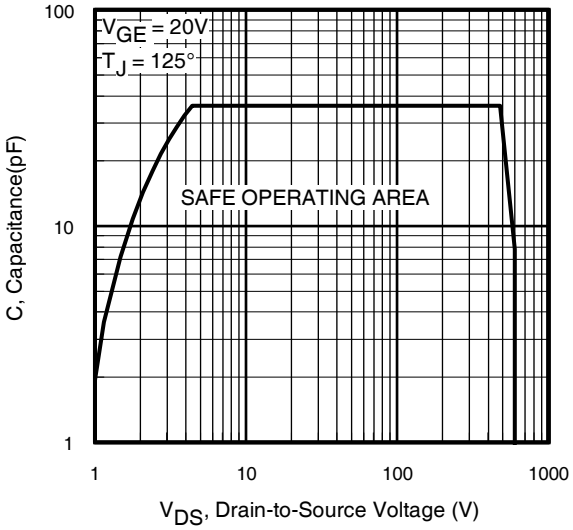


Fig. 12 - Turn-Off SOA

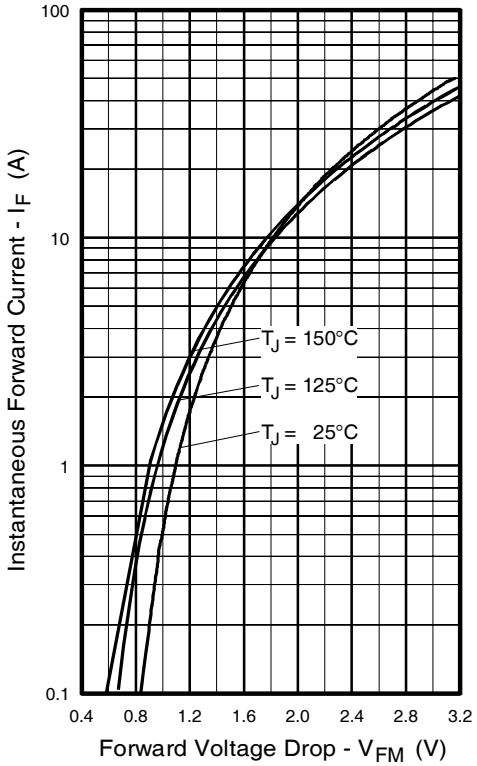


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

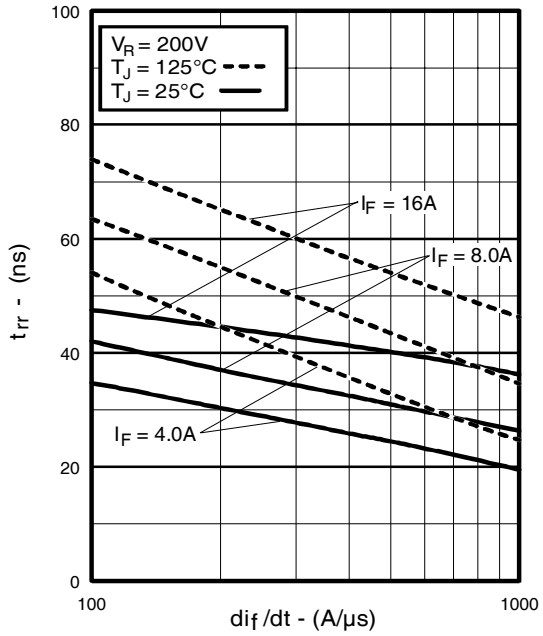


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

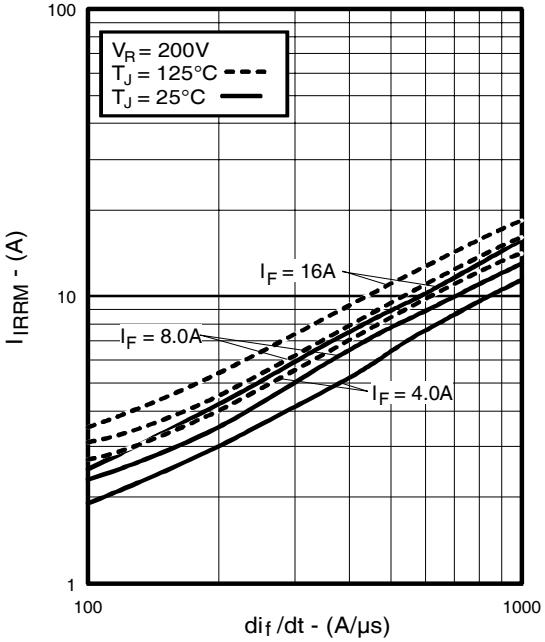


Fig. 15 - Typical Recovery Current vs. di_f/dt

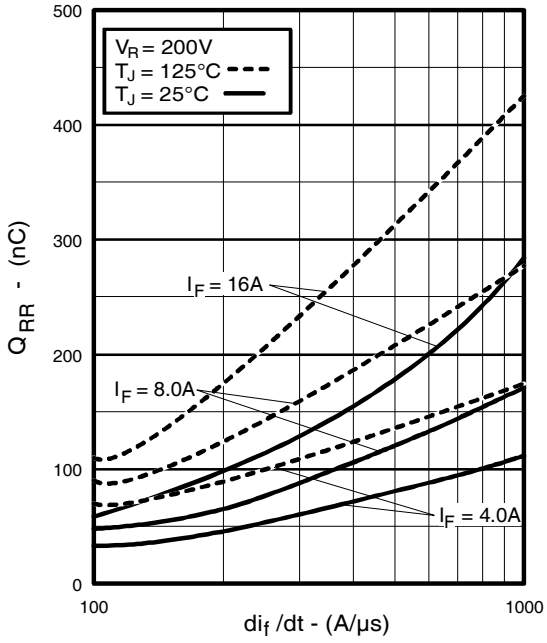


Fig. 16 - Typical Stored Charge vs. di_f/dt

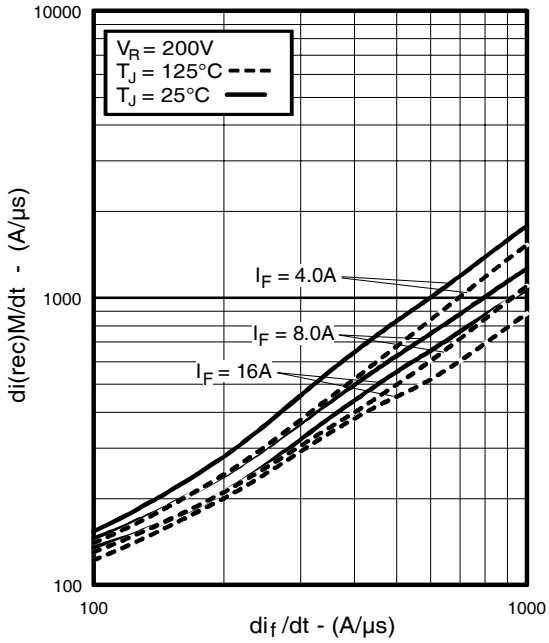


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

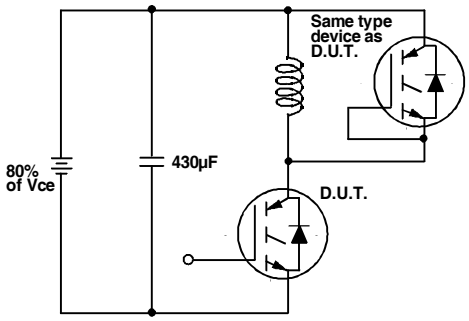


Fig. 18a - Test Circuit for Measurement of I_{LM}, E_{on}, $E_{off(diode)}$, t_{rr}, Q_{rr}, I_{rr}, $t_{d(on)}$, t_r, $t_{d(off)}$, t_f

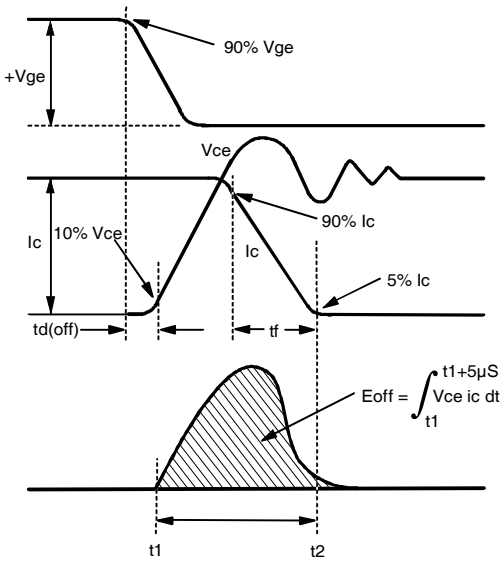


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off}, $t_{d(off)}$, t_f

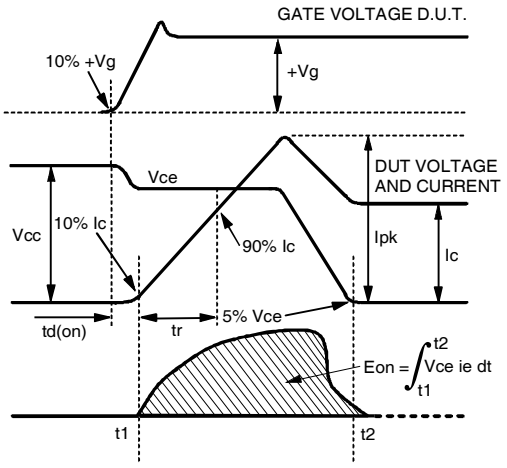


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on}, $t_{d(on)}$, t_r

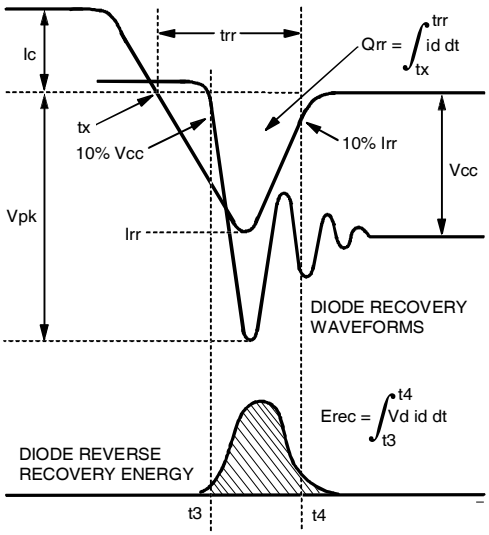


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec}, t_{rr}, Q_{rr}, I_{rr}

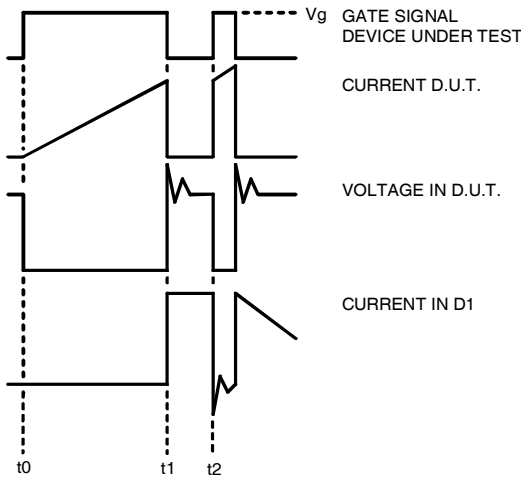


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

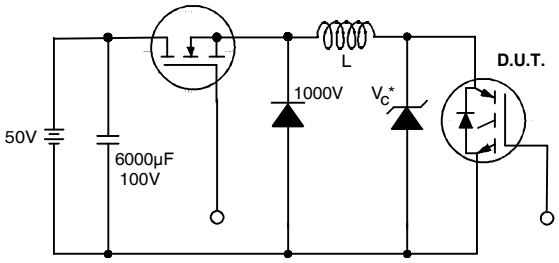
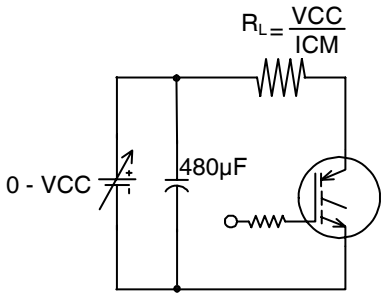


Figure 19. Clamped Inductive Load Test Circuit



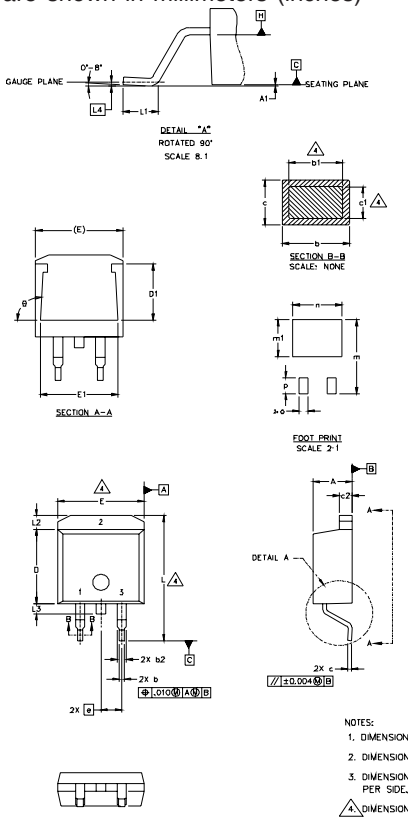
Pulsed Collector Current
Test Circuit

Figure 20. Pulsed Collector Current Test Circuit

International
IOR Rectifier

D²Pak Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1		0.127		.005	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	4
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2		1.65		.065	
L3	1.27	1.78	.050	.070	
L4	0.25 BSC		.010 BSC		
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
θ	90°	93°	90°	93°	

LEAD ASSIGNMENTS

HEXFET	IGBTs, CoPACK	DIODES
1.– GATE	1.– GATE	1.– ANODE *
2.– DRAIN	2.– COLLECTOR	2.– CATHODE
3.– SOURCE	3.– EMITTER	3.– ANODE

* PART DEPENDENT.

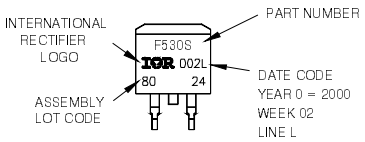
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M–1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

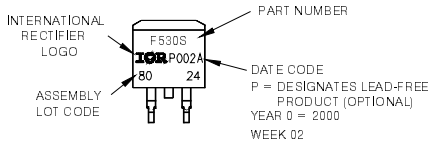
D²Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE 'L'

Note: 'P' in assembly line position indicates 'Lead-Free'



OR



Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Notes:

① Repetitive rating: V_{GE}=20V; pulse width limited by maximum junction temperature (figure 20)

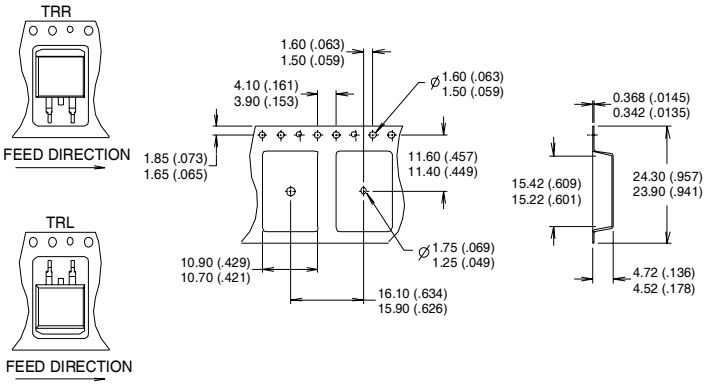
② V_{CC}=80%(V_{CES}), V_{GE}=20V, L=10µH, R_G = 50Ω (figure 19)

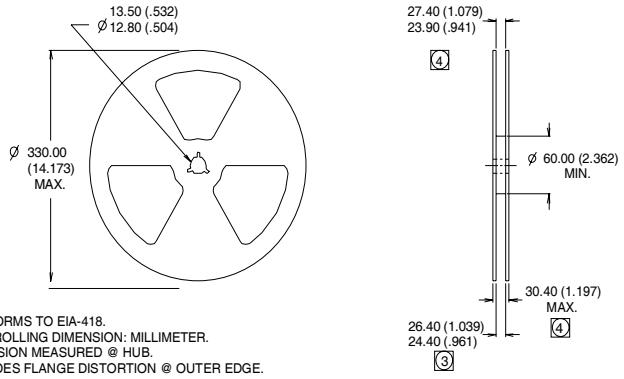
③ Pulse width ≤ 80µs; duty factor ≤ 0.1%.

④ Pulse width 5.0µs, single shot.

D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)





NOTES :
1. COMFORMS TO EIA-418.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION MEASURED @ HUB.
4. INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Data and specifications subject to change without notice.
This product has been designed and qualified for the industrial market.
Qualification Standards can be found on IR's Web site.

International
IOR Rectifier

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Visit us at www.irf.com for sales contact information. 01/2010